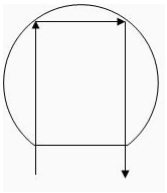
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None/SEMI Standard	
	5.0	Overall Thickness	339.00 +/- 12.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<170.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<170.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Lasermarking	Custom small scribe: on wafer backside, on left of the flat. Dimensions 7mm x 1mm. See attachment	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0	Handle Thickness	300.00 +/- 10.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Wafer Vendor
	16.0	Handle Dopant	Boron	Wafer Vendor
	17.0	Handle Resistivity	0.01 - 0.04 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide and laser marking.	Guaranteed by process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	24.0	Nominal Thickness	35.00 +/- 1.00 µm	FTIR 9 point, 100%
	25.0	Distance to device silicon edge from wafer edge	<= 1.5mm	Typical by Process
	26.0	Device Doping Type	P	Wafer Vendor
	27.0	Device Dopant	Boron	Wafer Vendor
	28.0	Device Resistivity	0.01- 0.04 Ohmcm	Wafer Vendor
	29.0	Voids	0	Bright Light, 100% (note 2)
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)
	32.0	Device Field Oxidation	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%

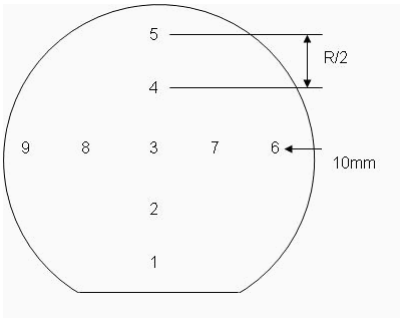
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information